

FEATURES

- Double Side Cooling
- High Surge Capability

APPLICATIONS

- High Power Drives
- High Voltage Power Supplies
- Static Switches

VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages V_{DRM} and V_{RRM} V	Conditions
DCR750D24	2400	$T_{vj} = -40^{\circ}\text{C}$ to 125°C , $I_{DRM} = I_{RRM} = 50\text{mA}$, $V_{DRM}, V_{RRM} t_p = 10\text{ms}$, $V_{DSM} \& V_{RSM} =$ $V_{DRM} \& V_{RRM} + 100\text{V}$ respectively
DCR750D22	2200	
DCR750D20	2000	

Lower voltage grades available.

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR750D24

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

KEY PARAMETERS

V_{DRM}	2400 V
$I_{T(AV)}$	750 A
I_{TSM}	10000 A
dV/dt^*	1000 V/ μs
dI/dt	200 A/ μs

* Higher dV/dt selections available

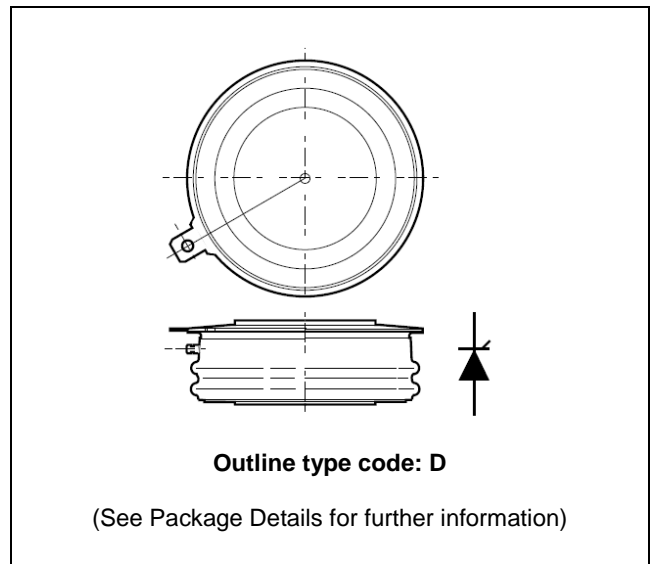


Fig. 1 Package outline

CURRENT RATINGS

T_{case} = 60°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Side Cooled				
I _{T(AV)}	Mean on-state current	Half wave resistive load	750	A
I _{T(RMS)}	RMS value	-	1180	A
I _T	Continuous (direct) on-state current	-	1060	A

SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
I _{TSM}	Surge (non-repetitive) on-state current	10ms half sine, T _{case} = 125°C	10.0	kA
I ² t	I ² t for fusing	V _R = 0	0.50	MA ² s

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions	Min.	Max.	Units
R _{th(j-c)}	Thermal resistance – junction to case	Double side cooled	-	0.035	°C/W
R _{th(c-h)}	Thermal resistance – case to heatsink	Double side cooled	-	0.01	°C/W
T _{vj}	Virtual junction temperature	Blocking V _{DRM} / V _{RRM}	-	125	°C
T _{stg}	Storage temperature range		-40	140	°C
F _m	Clamping force		8	12	kN

DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Conditions	Min.	Max.	Units	
I_{RRM}/I_{DRM}	Peak reverse and off-state current	At V_{RRM}/V_{DRM} , $T_{case} = 125^{\circ}C$	-	50	mA	
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V_{DRM} , $T_j = 125^{\circ}C$, gate open	1000	-	V/ μs	
di/dt	Rate of rise of on-state current	From 67% V_{DRM} to 1000A Gate source 30V, 10 Ω , $t_r < 0.5\mu s$, $T_j = 125^{\circ}C$	Repetitive 50Hz	-	200	A/ μs
			Non-repetitive	-	1000	A/ μs
V_T	On-state voltage	$I_T = 1500A$, $T_{case} = 125^{\circ}C$		2.00	V	
$V_{T(TO)}$	Threshold voltage – Low level	$T_{case} = 125^{\circ}C$	-	0.92	V	
r_T	On-state slope resistance – Low level	$T_{case} = 125^{\circ}C$	-	0.72	m Ω	
t_{gd}	Delay time	$V_D = 67\% V_{DRM}$, gate source 30V, 10 Ω $t_r = 0.5\mu s$, $T_j = 25^{\circ}C$	-	3.0	μs	
t_q	Turn-off time	$T_j = 125^{\circ}C$, $V_R = 100V$, $di/dt = 10A/\mu s$, $dV_{DR}/dt = 20V/\mu s$ linear to 67% V_{DRM}	-	150	μs	
Q_S	Stored charge	$I_T = 1000A$, $t_p = 1000\mu s$, $T_j = 125^{\circ}C$, $di/dt = 10A/\mu s$,	-	2300	μC	
I_{RR}	Reverse recovery current		-	125	A	
I_L	Latching current	$T_j = 25^{\circ}C$,	-	1	A	
I_H	Holding current	$T_j = 25^{\circ}C$,	-	200	mA	

GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
V_{GT}	Gate trigger voltage	$V_{DRM} = 5V$, $T_{case} = 25^{\circ}C$	3	V
V_{GD}	Gate non-trigger voltage	At 40% V_{DRM} , $T_{case} = 125^{\circ}C$	TBD	V
I_{GT}	Gate trigger current	$V_{DRM} = 5V$, $T_{case} = 25^{\circ}C$	300	mA
I_{GD}	Gate non-trigger current	At 40% V_{DRM} , $T_{case} = 125^{\circ}C$	TBD	mA

CURVES

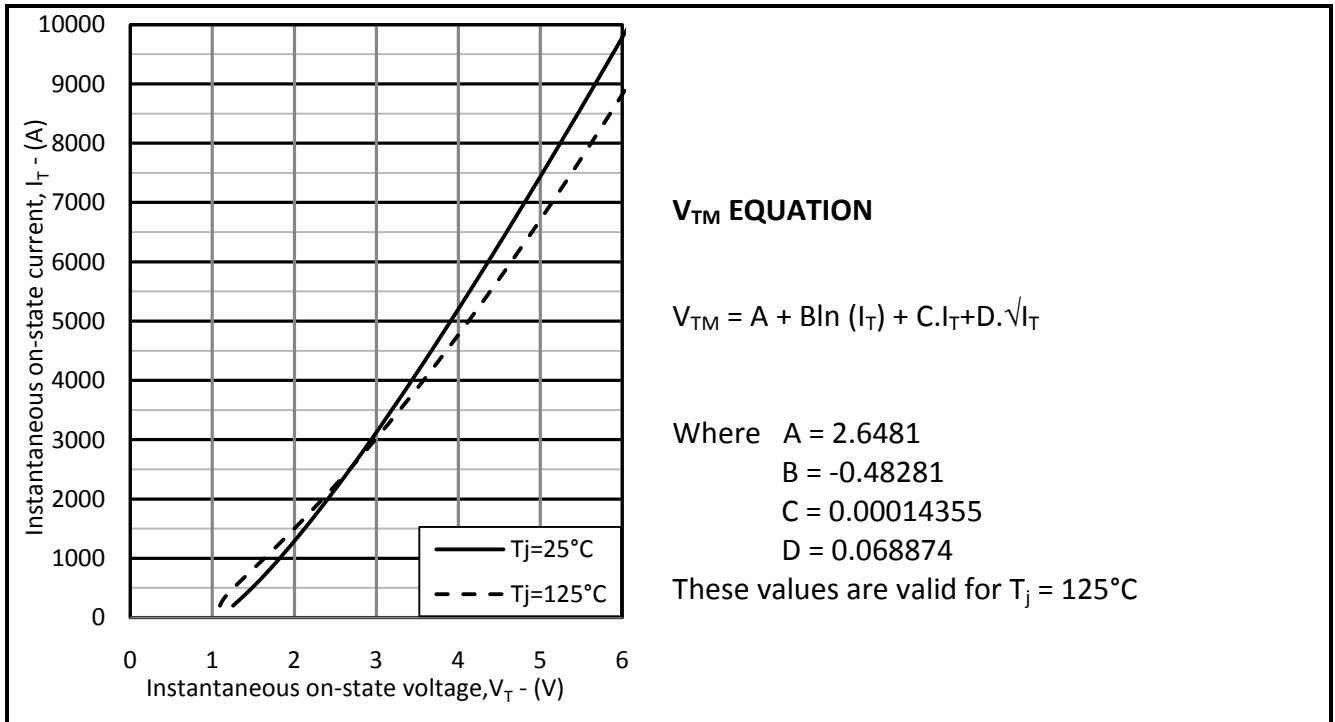


Fig.2 Maximum & minimum on-state characteristics

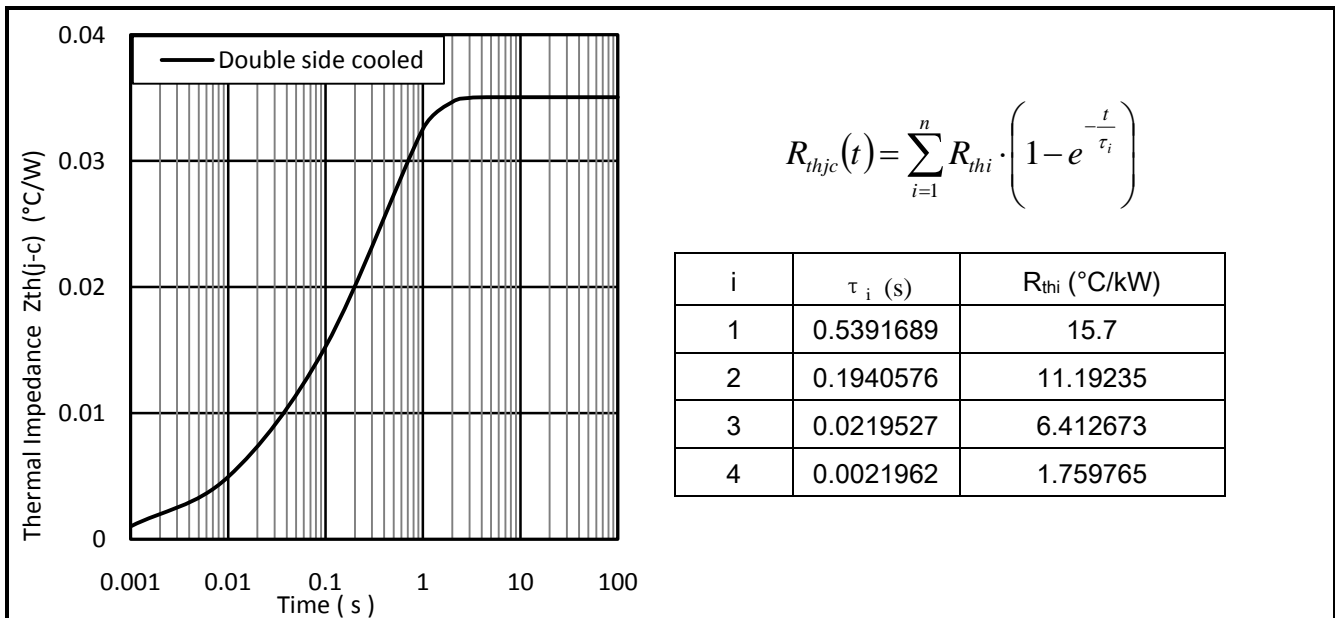


Fig.3 Maximum (limit) transient thermal impedance – junction to case (°C/W)

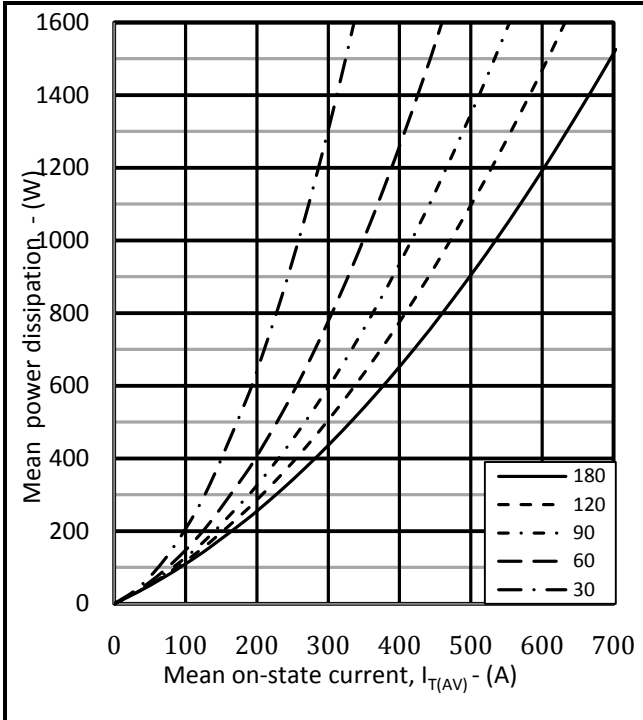


Fig.4 On-state power dissipation – sine wave

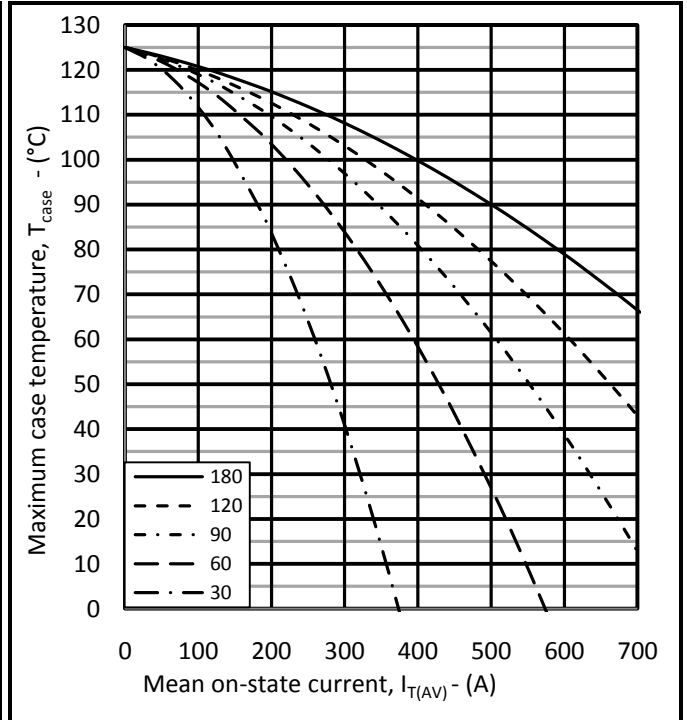


Fig.5 Maximum permissible case temperature, double side cooled – sine wave

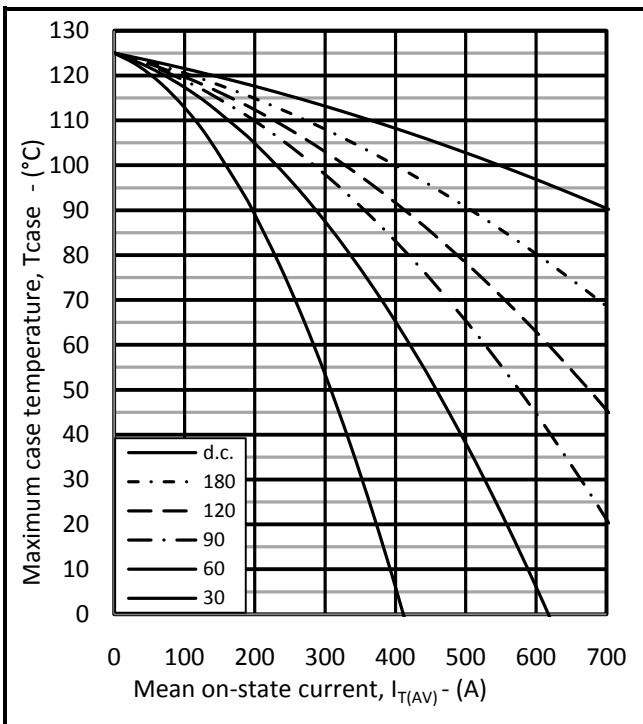


Fig.6 Maximum permissible case temperature, double side cooled – rectangular wave

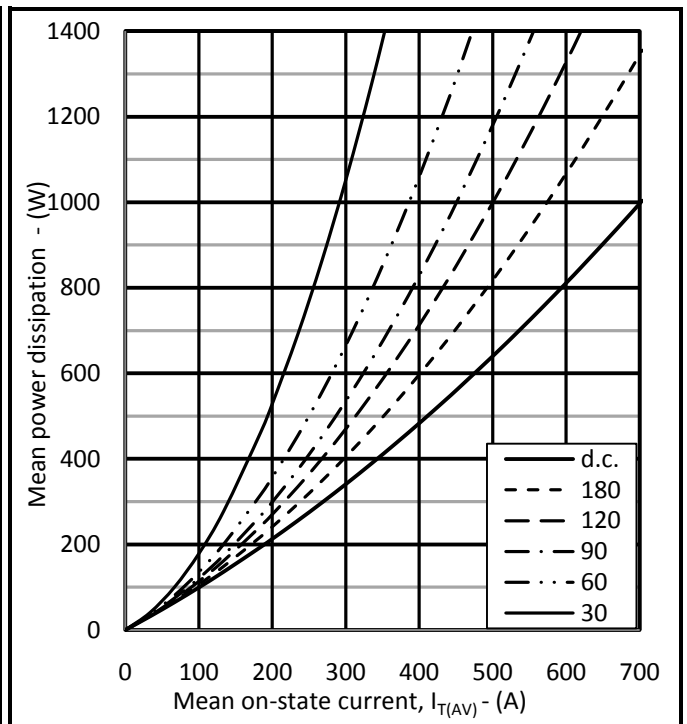


Fig.7 On-state power dissipation – rectangular wave

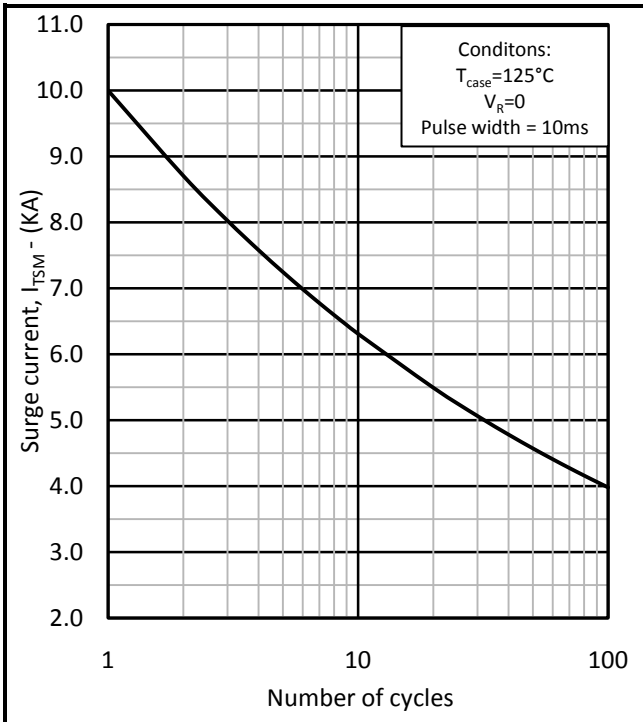


Fig.8 Multi-cycle surge current

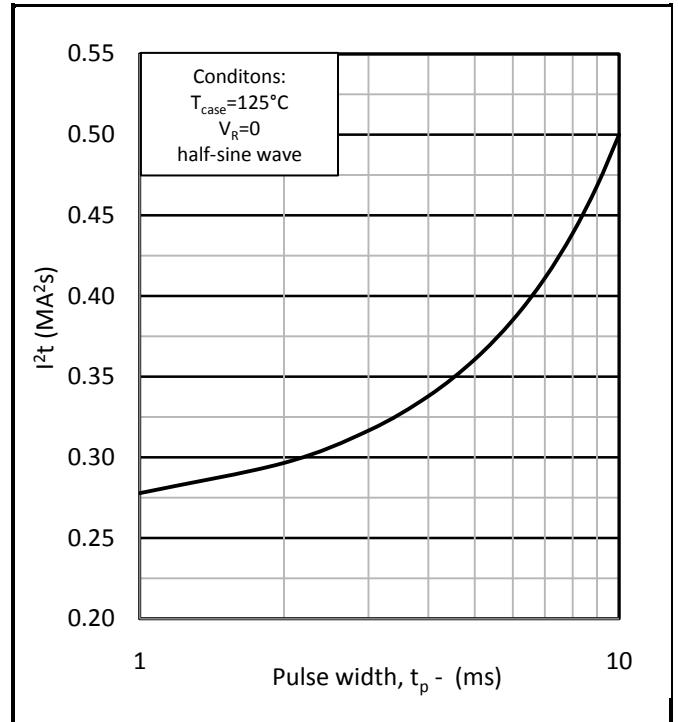


Fig.9 Single-cycle I^2t

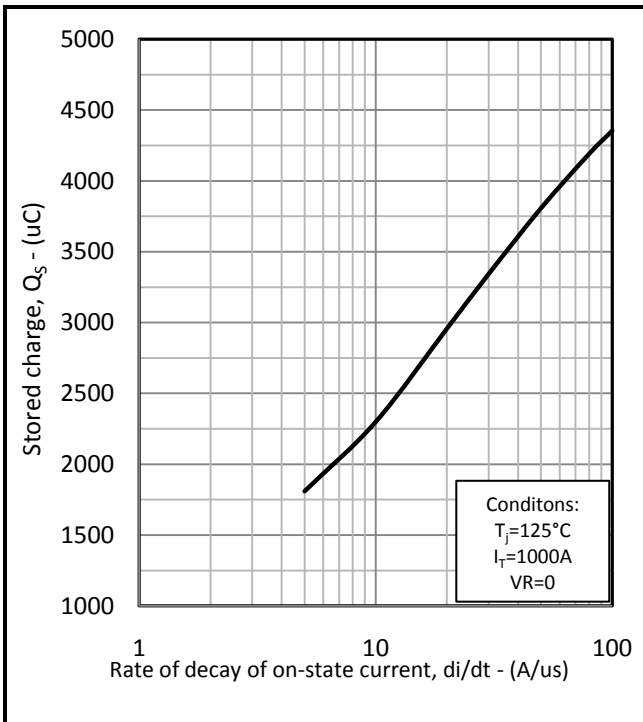


Fig.10 Stored charge vs di/dt

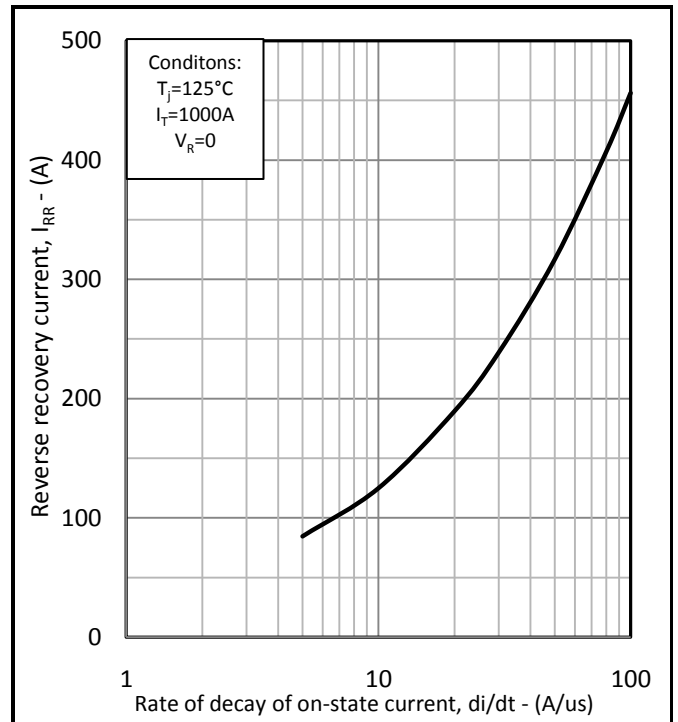


Fig.11 Reverse recovery current vs di/dt

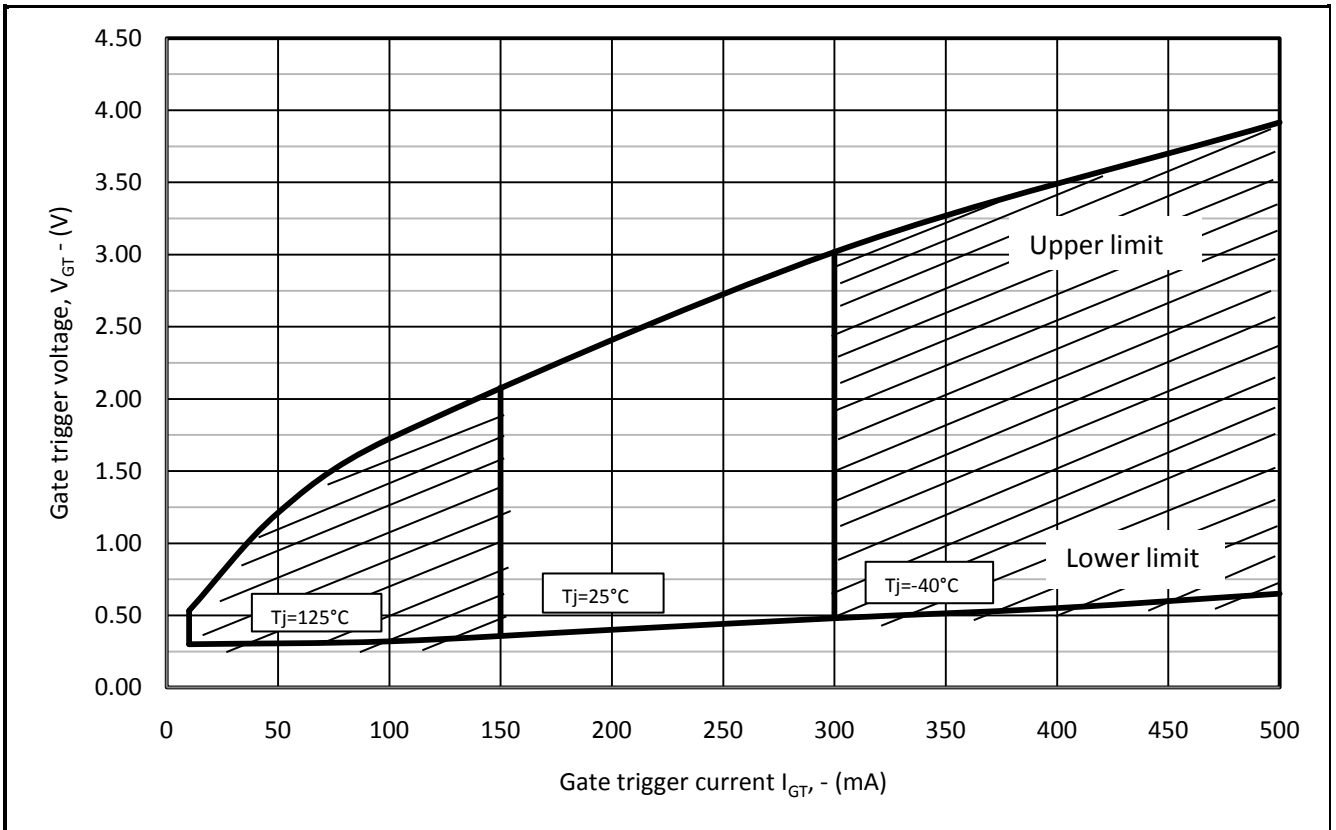
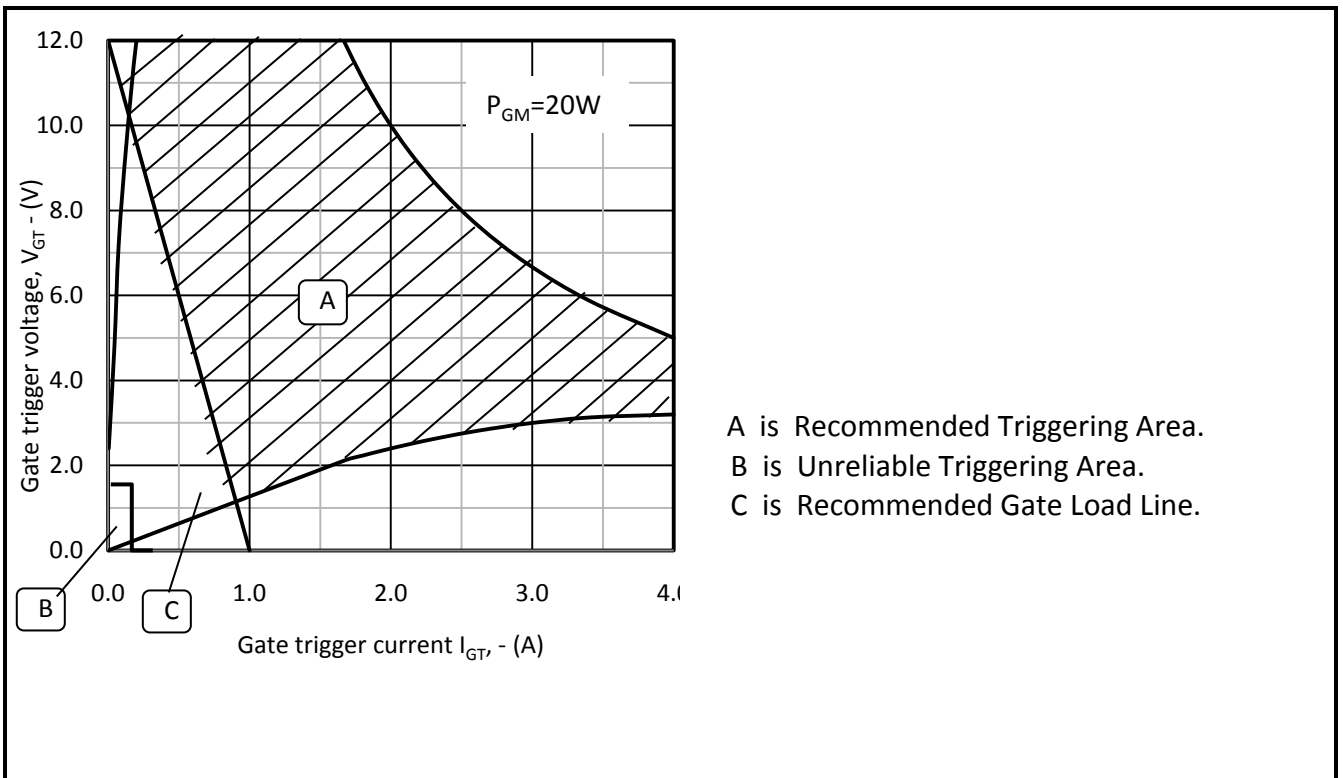


Fig.12 Gate characteristics



A is Recommended Triggering Area.
B is Unreliable Triggering Area.
C is Recommended Gate Load Line.

Fig.13 Gate characteristics

PACKAGE DETAILS

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.

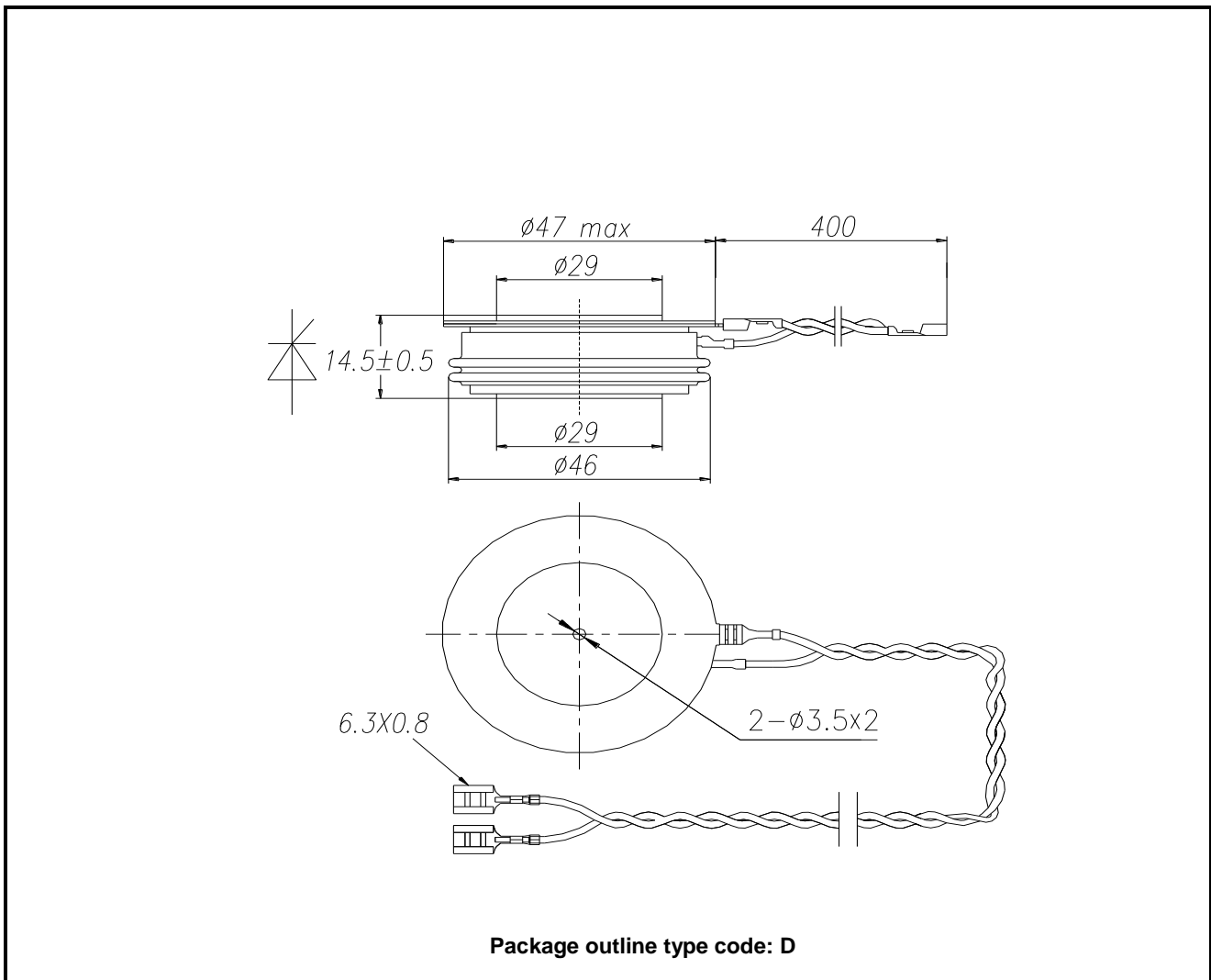


Fig.14 Package outline

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